

# FGPF10N60UNDF

## 600V, 10A Short Circuit Rated IGBT

### Features

- Short circuit rated 10us
- High current capability
- High input impedance
- Fast switching
- RoHS compliant

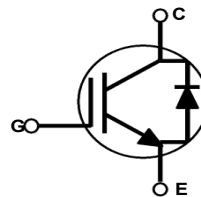
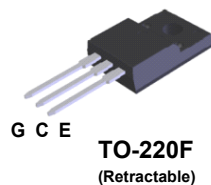


### Applications

- Home appliance inverter-driven application  
- Air Conditioner, Washing Machine, Refrigerator, Dish Washer
- Industrial Inverter - Sewing Machine, CNC

### General Description

Using advanced NPT IGBT Technology, Fairchild's the NPT IGBTs offer the optimum performance for low power inverter-driven applications where low-losses and short circuit ruggedness feature are essential.



### Absolute Maximum Ratings

| Symbol      | Description   | Ratings     | Units            |
|-------------|---|-------------|------------------|
| $V_{CES}$   | Collector to Emitter Voltage                          | 600         | V                |
| $V_{GES}$   | Gate to Emitter Voltage                               | $\pm 20$    | V                |
| $I_C$       | Collector Current @ $T_C = 25^\circ\text{C}$          | 20          | A                |
|             | Collector Current @ $T_C = 100^\circ\text{C}$         | 10          | A                |
| $I_{CM(1)}$ | Pulsed Collector Current @ $T_C = 25^\circ\text{C}$   | 30          | A                |
| $I_F$       | Diode Forward Current @ $T_C = 25^\circ\text{C}$      | 10          | A                |
| $P_D$       | Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$  | 42          | W                |
|             | Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$ | 17          | W                |
| $T_J$       | Operating Junction Temperature                        | -55 to +150 | $^\circ\text{C}$ |
| $T_{stg}$   | Storage Temperature Range                             | -55 to +150 | $^\circ\text{C}$ |

**Notes:**  
1: Repetitive rating: Pulse width limited by max. junction temperature

### Thermal Characteristics

| Symbol                  | Parameter  | Typ. | Max. | Units                     |
|-------------------------|--|------|------|---------------------------|
| $R_{\theta JC}$ (IGBT)  | Thermal Resistance, Junction to Case                   | -    | 3.0  | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JC}$ (Diode) | Thermal Resistance, Junction to Case                   | -    | 5.6  | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$         | Thermal Resistance, Junction to Ambient (PCB Mount)(2) | -    | 62.5 | $^\circ\text{C}/\text{W}$ |

**Notes:**  
2: Mountde on 1" square PCB (FR4 or G-10 material)

## Package Marking and Ordering Information

| Device Marking | Device        | Package | Packaging Type | Qty per Tube | Max Qty per Box |
|----------------|---------------|---------|----------------|--------------|-----------------|
| FGPF10N60UNDF  | FGPF10N60UNDF | TO-220F | Tube           | 50ea         | -               |

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

| Symbol                           | Parameter                               | Test Conditions   | Min. | Typ. | Max. | Units |
|----------------------------------|---|---|------|------|------|-------|
| <b>Off Characteristics</b>       |   |   |      |      |      |       |
| BV <sub>CE(S)</sub>              | Collector to Emitter Breakdown Voltage  | V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA  | 600  | -    | -    | V     |
| I <sub>CE(S)</sub>               | Collector Cut-Off Current               | V <sub>CE</sub> = V <sub>CE(S)</sub> , V <sub>GE</sub> = 0V   | -    | -    | 1    | mA    |
| I <sub>GES</sub>                 | G-E Leakage Current                     | V <sub>GE</sub> = V <sub>GES</sub> , V <sub>CE</sub> = 0V   | -    | -    | ±10  | μA    |
| <b>On Characteristics</b>        |   |   |      |      |      |       |
| V <sub>GE(th)</sub>              | G-E Threshold Voltage                   | I <sub>C</sub> = 10mA, V <sub>CE</sub> = V <sub>GE</sub>  | 5.5  | 6.8  | 8.5  | V     |
| V <sub>CE(sat)</sub>             | Collector to Emitter Saturation Voltage | I <sub>C</sub> = 10A, V <sub>GE</sub> = 15V   | -    | 2    | 2.45 | V     |
|                                  |   | I <sub>C</sub> = 10A, V <sub>GE</sub> = 15V,<br>T <sub>C</sub> = 125°C  | -    | 2.3  | -    | V     |
| <b>Dynamic Characteristics</b>   |   |   |      |      |      |       |
| C <sub>ies</sub>                 | Input Capacitance                       | V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V,<br>f = 1MHz  | -    | 517  |      | pF    |
| C <sub>oes</sub>                 | Output Capacitance                      |   | -    | 65   |      | pF    |
| C <sub>res</sub>                 | Reverse Transfer Capacitance            |   | -    | 20   |      | pF    |
| <b>Switching Characteristics</b> |   |   |      |      |      |       |
| t <sub>d(on)</sub>               | Turn-On Delay Time                      | V <sub>CC</sub> = 400V, I <sub>C</sub> = 10A,<br>R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15V,<br>Inductive Load, T <sub>C</sub> = 25°C  | -    | 8.0  |      | ns    |
| t <sub>r</sub>                   | Rise Time                               |   | -    | 6.3  |      | ns    |
| t <sub>d(off)</sub>              | Turn-Off Delay Time                     |   | -    | 52.2 |      | ns    |
| t <sub>f</sub>                   | Fall Time                               |   | -    | 19.1 | 24.8 | ns    |
| E <sub>on</sub>                  | Turn-On Switching Loss                  |   | -    | 0.15 |      | mJ    |
| E <sub>off</sub>                 | Turn-Off Switching Loss                 |   | -    | 0.05 |      | mJ    |
| E <sub>ts</sub>                  | Total Switching Loss                    |   | -    | 0.2  |      | mJ    |
| t <sub>d(on)</sub>               | Turn-On Delay Time                      | V <sub>CC</sub> = 400V, I <sub>C</sub> = 10A,<br>R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 15V,<br>Inductive Load, T <sub>C</sub> = 125°C | -    | 8.1  |      | ns    |
| t <sub>r</sub>                   | Rise Time                               |   | -    | 7.3  |      | ns    |
| t <sub>d(off)</sub>              | Turn-Off Delay Time                     |   | -    | 55.1 |      | ns    |
| t <sub>f</sub>                   | Fall Time                               |   | -    | 34.2 |      | ns    |
| E <sub>on</sub>                  | Turn-On Switching Loss                  |   | -    | 0.22 |      | mJ    |
| E <sub>off</sub>                 | Turn-Off Switching Loss                 |   | -    | 0.08 |      | mJ    |
| E <sub>ts</sub>                  | Total Switching Loss                    |   | -    | 0.3  |      | mJ    |
| T <sub>sc</sub>                  | Short Circuit Withstand Time            | V <sub>CC</sub> = 350V,<br>R <sub>G</sub> = 100Ω, V <sub>GE</sub> = 15V,<br>T <sub>C</sub> = 150°C                                      | 10   | -    | -    | μs    |

**Electrical Characteristics of the IGBT**  $T_C = 25^\circ\text{C}$  unless otherwise noted

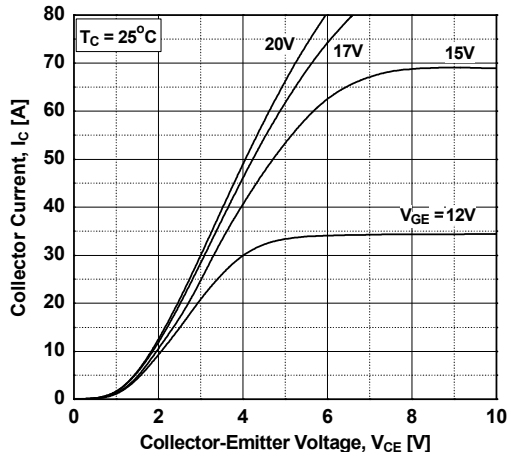
| Symbol   | Parameter                | Test Conditions  | Min. | Typ. | Max | Units |
|----------|--------------------------|--|------|------|-----|-------|
| $Q_g$    | Total Gate Charge        | $V_{CE} = 400\text{V}, I_C = 10\text{A},$<br>$V_{GE} = 15\text{V}$ | -    | 37   |     | nC    |
| $Q_{ge}$ | Gate to Emitter Charge   |  | -    | 5    |     | nC    |
| $Q_{gc}$ | Gate to Collector Charge |  | -    | 21   |     | nC    |

**Electrical Characteristics of the Diode**  $T_C = 25^\circ\text{C}$  unless otherwise noted

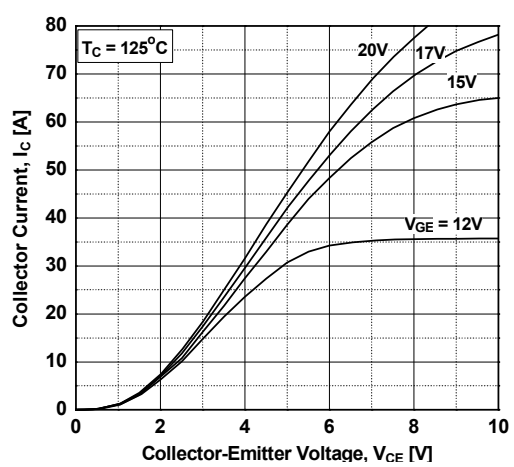
| Symbol   | Parameter                     | Test Conditions                                       | Min.                      | Typ. | Max  | Units |    |
|----------|-------------------------------|---|---------------------------|------|------|-------|----|
| $V_{FM}$ | Diode Forward Voltage         | $I_F = 10\text{A}$                                    | $T_C = 25^\circ\text{C}$  | -    | 1.8  | 2.2   | V  |
|          |                               |   | $T_C = 125^\circ\text{C}$ | -    | 1.7  |       |    |
| $t_{rr}$ | Diode Reverse Recovery Time   | $I_F = 10\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$ | $T_C = 25^\circ\text{C}$  | -    | 37.7 |       | ns |
|          |                               |   | $T_C = 125^\circ\text{C}$ | -    | 78.9 |       |    |
| $Q_{rr}$ | Diode Reverse Recovery Charge | $I_F = 10\text{A}, dI_F/dt = 200\text{A}/\mu\text{s}$ | $T_C = 25^\circ\text{C}$  | -    | 75   |       | nC |
|          |                               |   | $T_C = 125^\circ\text{C}$ | -    | 221  |       |    |

## Typical Performance Characteristics

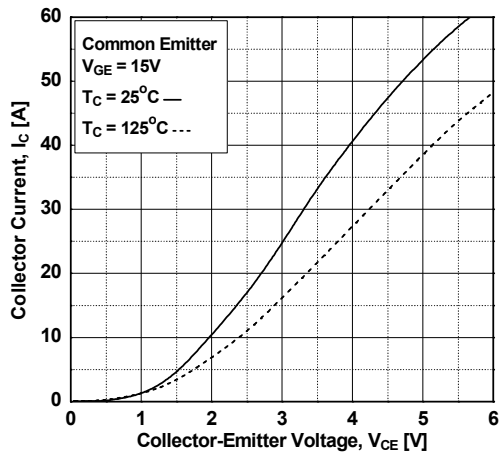
**Figure 1. Typical Output Characteristics**



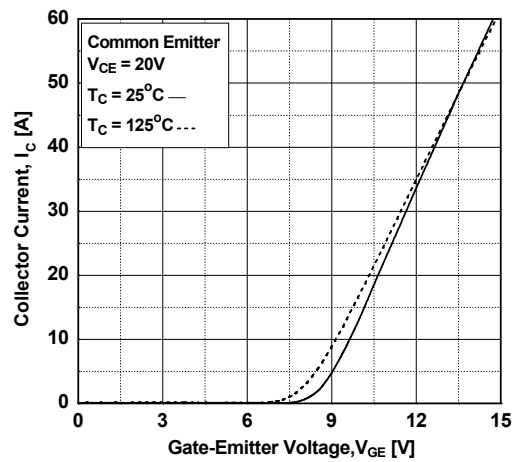
**Figure 2. Typical Output Characteristics**



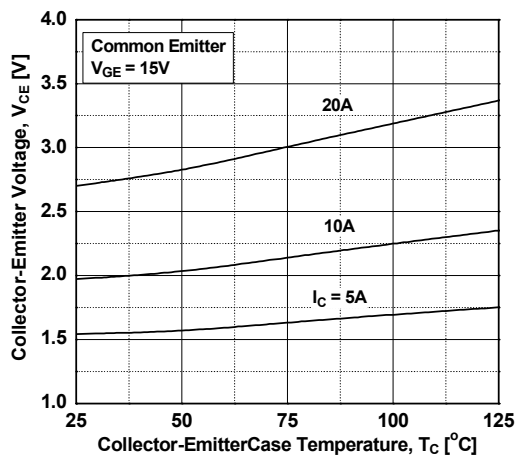
**Figure 3. Typical Saturation Voltage Characteristics**



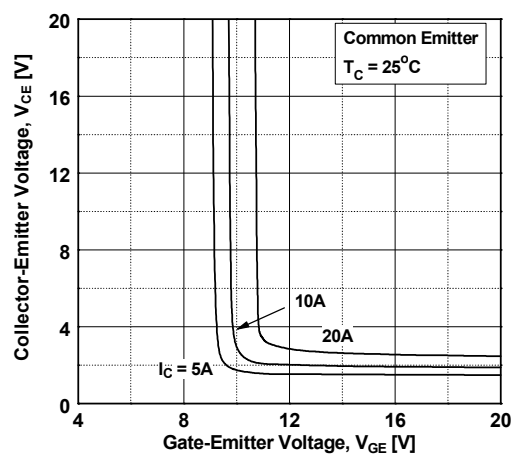
**Figure 4. Transfer Characteristics**



**Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level**



**Figure 6. Saturation Voltage vs. Vge**



Typical Performance Characteristics

Typical Performance Characteristics

Figure 7. Saturation Voltage vs.  $V_{GE}$

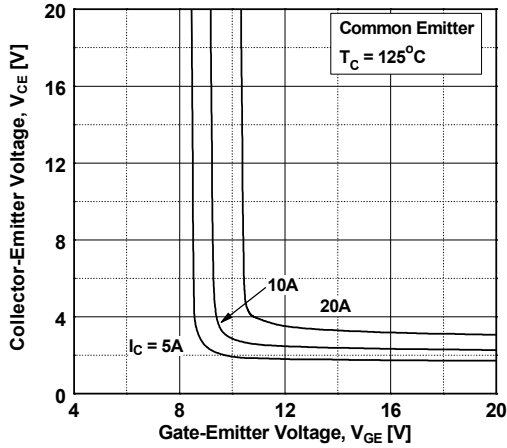


Figure 8. Capacitance Characteristics

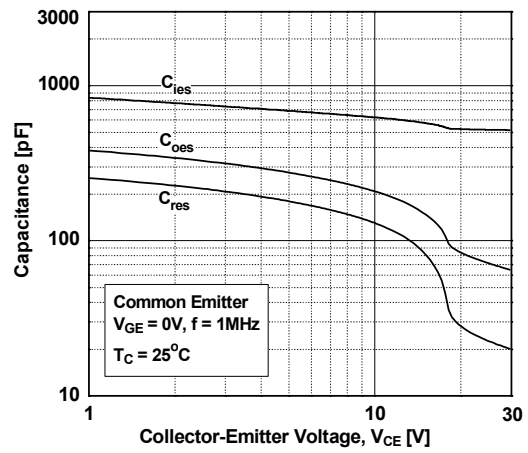


Figure 9. Gate charge Characteristics

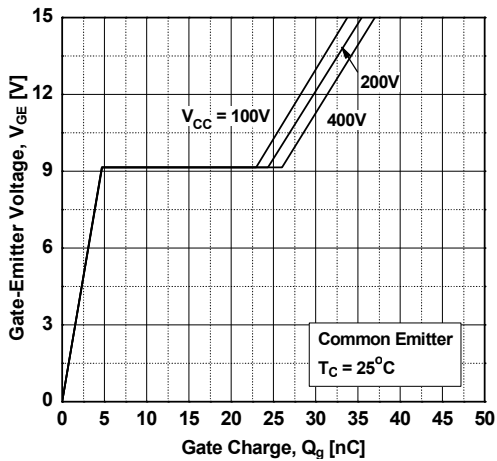


Figure 10. SOA Characteristics

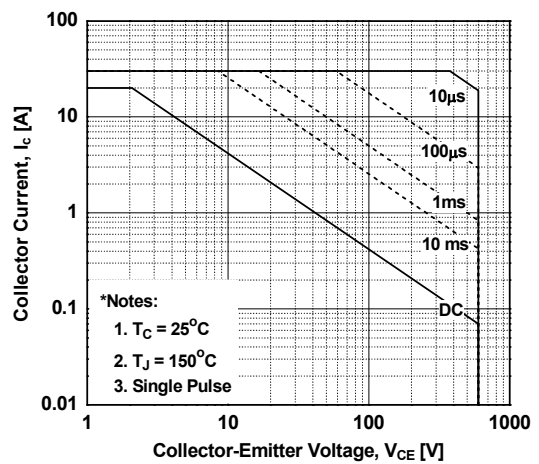


Figure 11. Turn-on Characteristics vs. Gate Resistance

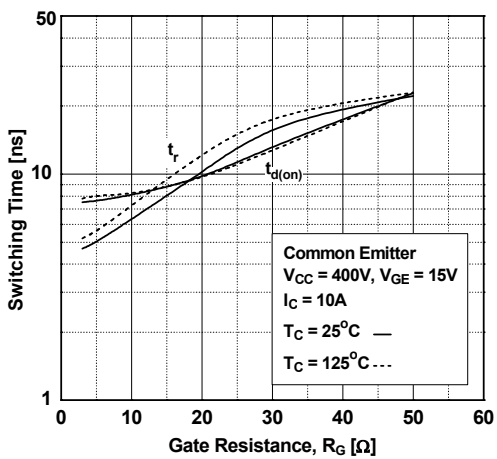
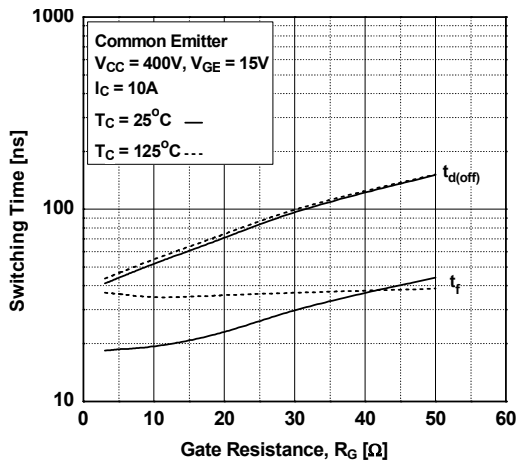
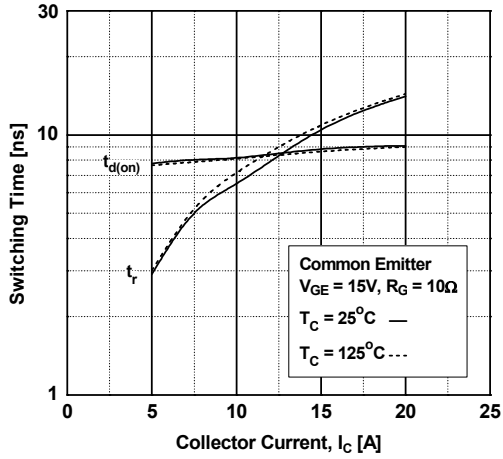


Figure 12. Turn-off Characteristics vs. Gate Resistance

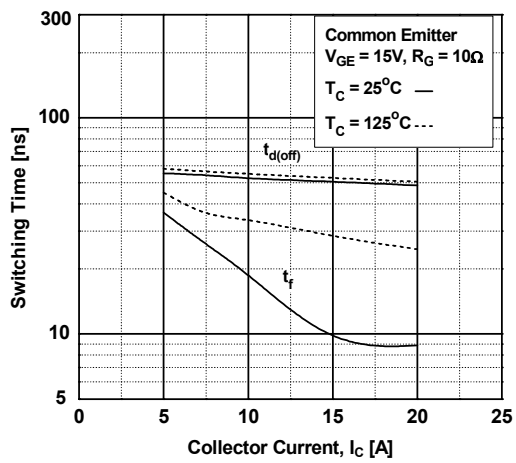


### Typical Performance Characteristics

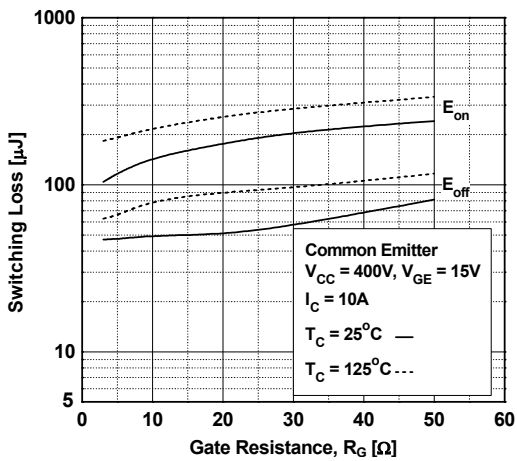
**Figure 13. Turn-on Characteristics vs. Collector Current**



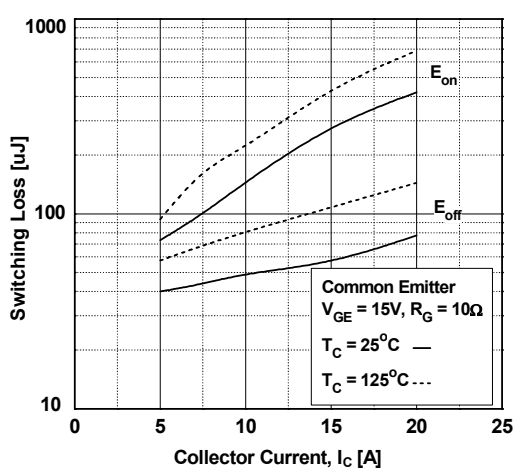
**Figure 14. Turn-off Characteristics vs. Collector Current**



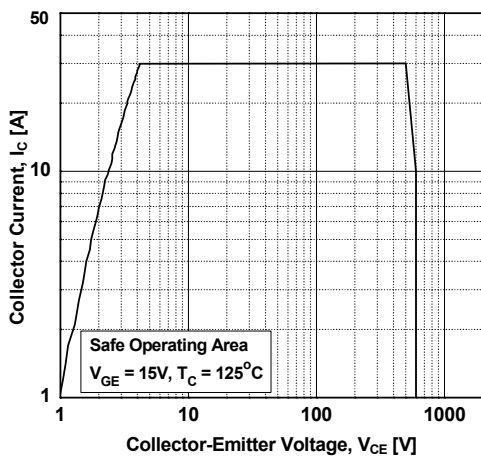
**Figure 15. Switching Loss vs. Gate Resistance**



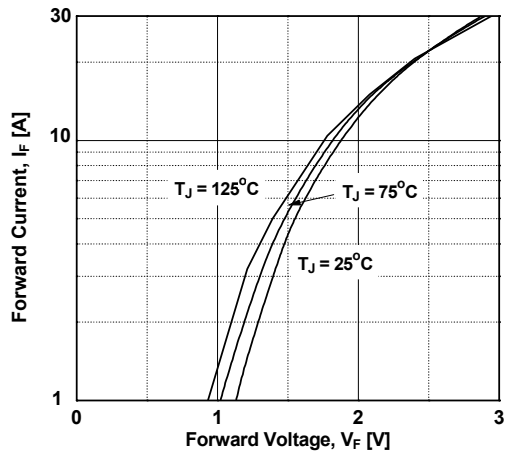
**Figure 16. Switching Loss vs Collector Current**



**Figure 17. Turn off Switching SOA Characteristics**



**Figure 18. Forward Characteristics**



## Typical Performance Characteristics

Figure 19. Reverse Recovery Current

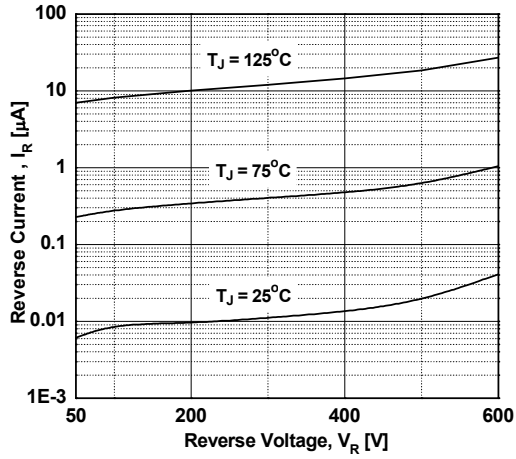


Figure 20. Stored Charge

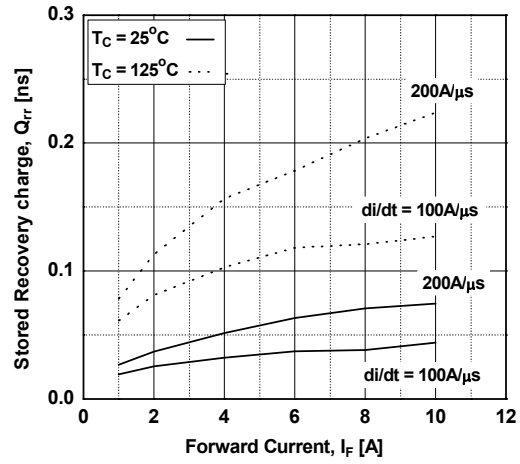


Figure 21. Reverse Recovery Time

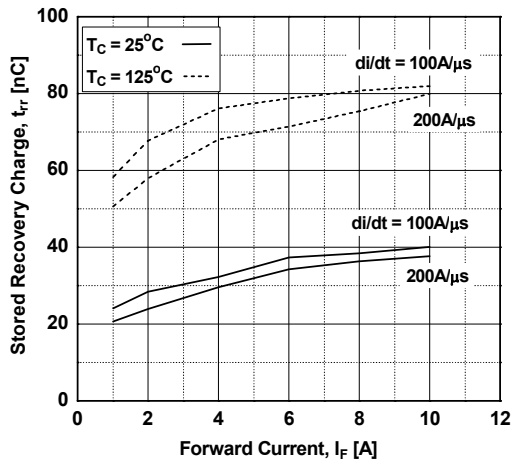
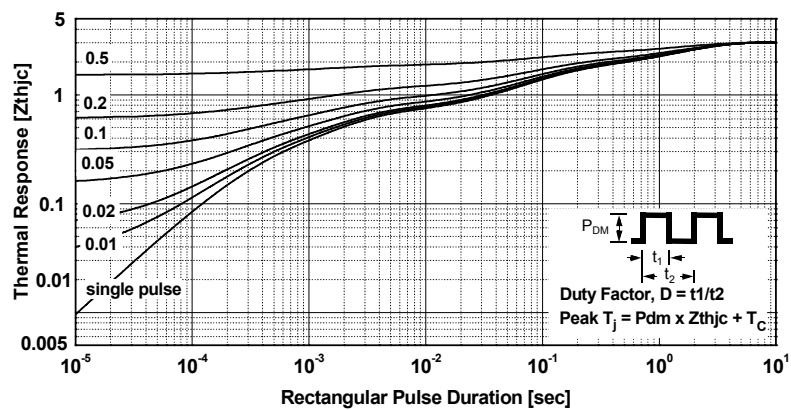
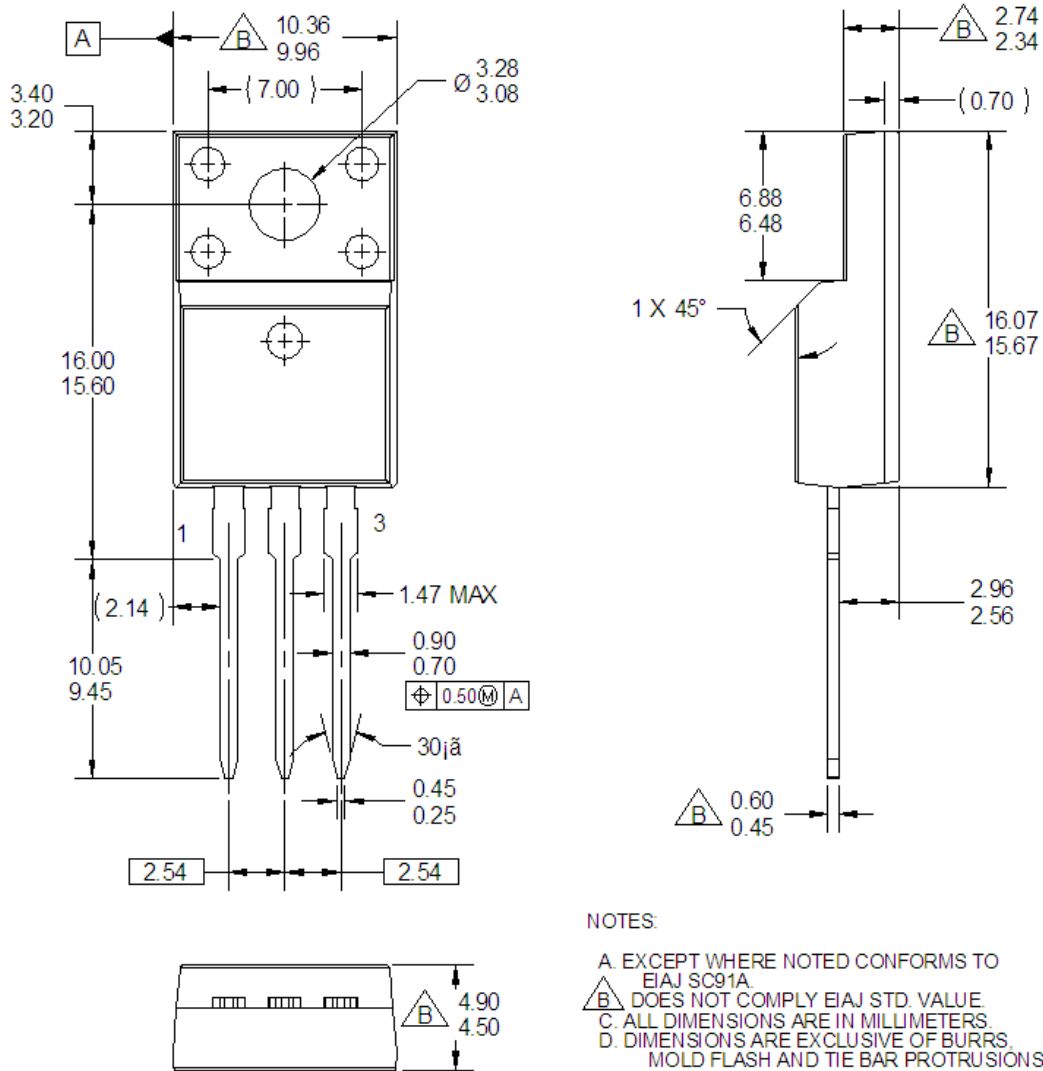


Figure 22. Transient Thermal Impedance of IGBT



**Mechanical Dimensions**

**TO-220F (Retractable)**



**NOTES:**

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. DRAWING FILE NAME: TO220M03REV1

**\* Front/Back Side Isolation Voltage : AC 2700V**







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### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331